



marks:

The preliminary amendment is being presented to make certain stylistic changes.

Please charge any other fees which might be due with respect to Sections 1.16 and 1.17 to the Deposit Account of Lerner & Greenberg P.A., No. 12-1099.

Respectfully submitted,



For Applicant(s)

AKD:cgm

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Marked-up version of the claims:

Claim 13 (amended). A method for producing [an] electronic [component] components with shielding, which comprises the steps of:

providing a semiconductor wafer functioning as a semiconductor substrate formed of a semiconductor material and having an active upper side for at least one integrated circuit for each of the electronic components and a passive rear side;

implanting impurities from the passive rear side of the semiconductor wafer for forming a buried layer being electrically conductive and having a surface area corresponding in size to a surface area of the passive rear side of the semiconductor substrate;

introducing an electrically conductive annular layer for each of the electronic components from the active upper side of the semiconductor wafer as far as the buried layer in an edge region of the integrated circuit;

producing the integrated circuit within the electrically conductive annular layer for each of the electronic components

in the semiconductor substrate defining a semiconductor chip
for each of the electronic components; and

packaging the semiconductor chip to form the electronic
[component] components with the shielding.

Claim 21 (amended). A method for producing [an] electronic
[component] components with shielding, which comprises the
following steps:

providing a semiconductor wafer functioning as a semiconductor
substrate having an active upper side for at least one
integrated component for each of the electronic components and
a passive rear side;

growing an electrically conductive layer formed of an
electrically conductive semiconductor material and thereafter
an electrically intrinsically conductive layer formed of an
electrically intrinsic conductive semiconductor material on
the active upper side of the semiconductor wafer by epitaxial
growth, the electrically conductive layer becoming a buried
layer adjacent the electrically intrinsically conductive
layer;

introducing an electrically conductive annular layer for each
of the electronic components from the active upper side of the

semiconductor wafer, the electrically conductive annular layer extending through the electrically intrinsically conductive layer as far as the buried layer, the electrically conductive annular layer disposed in an edge region of the semiconductor substrate;

producing the integrated circuit within the electrically conductive annular layer for each of the electronic components in the semiconductor substrate defining a semiconductor chip; and

packaging the individual conductor chips to form the electronic [component] components with the shielding.